**Product data sheet** 

## 1. General description

Ultrafast power diode in a SMC package.

### 2. Features and benefits

- Low on-state loss
- Low leakage current
- Low thermal resistance
- Surface-mountable package

# 3. Applications

- Switching mode power supply
- · High frequency rectifiers in buck and fly-back circuits
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)
- Terminal Adapter
- Inverter freewheeling and protection diode
- TV Power and LED Power

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Values	Unit				
Absolute	Absolute maximum rating							
$V_{RRM}$	repetitive peak reverse voltage		200	V				
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; square-wave pulse; T <sub>lead</sub> ≤ 148 °C; Fig. 1; Fig. 2; Fig. 3	3	Α				
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_{lead} \le$ 148 °C; square-wave pulse	6	Α				
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	160	Α				
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	176	А				

**Ultrafast power diode** 

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		v 14 A
2	A	anode	1 2	K A 001aaa020

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
MUR320	SMC	MUR320J	Reel	3000	SMCS	16-Aug-2017
		MUR320,118				

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking codes		
	Assembly factory: S	Assembly factory: E	
MUR320	320JS	320JE	

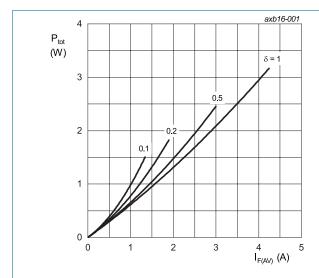
Ultrafast power diode

# 8. Limiting values

### **Table 5. Limiting values**

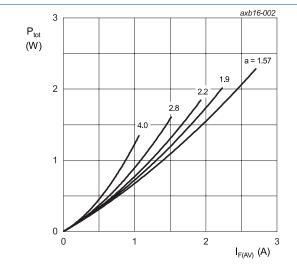
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		200	V
$V_{RWM}$	crest working reverse voltage		200	V
$V_R$	reverse voltage	DC	200	V
$I_{F(AV)}$	average forward current	$\delta$ = 0.5; square-wave pulse; $T_{lead} \le$ 148 °C; Fig. 1; Fig. 2; Fig. 3	3	Α
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_{lead} \le$ 148 °C; square-wave pulse	6	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	160	Α
		$t_p$ = 8.3 ms; $T_{J(init)}$ = 25 °C; sine-wave pulse	176	Α
T <sub>stg</sub>	storage temperature		-65 to 175	°C
T <sub>j</sub>	junction temperature		175	°C



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 0.573 \text{ V; } R_{\text{s}} = 0.0410 \text{ } \Omega \end{split}$$

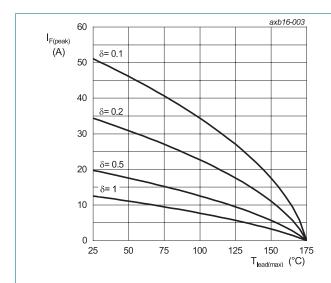
Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$   $V_o$  = 0.573 V;  $R_s$  = 0.0410  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

### Ultrafast power diode





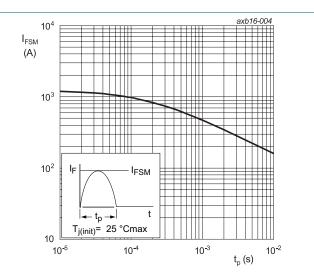


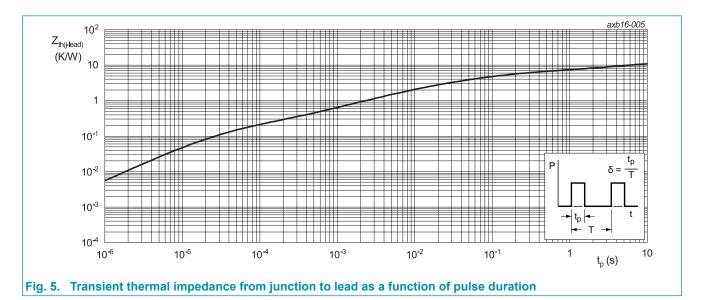
Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

Ultrafast power diode

### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	<u>Fig. 5</u>		-	-	11	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	70	-	K/W

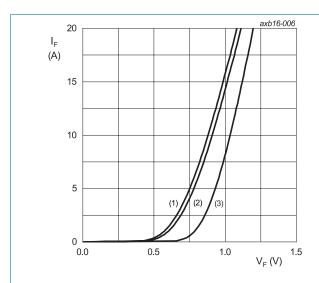


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## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
$V_{F}$	forward voltage	I <sub>F</sub> = 3 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	-	0.875	V
		I <sub>F</sub> = 3 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	-	0.71	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 200 V; T <sub>j</sub> = 25 °C		-	-	10	μΑ
		V <sub>R</sub> = 200 V; T <sub>j</sub> = 150 °C		-	-	400	μΑ
Dynamic	characteristics			,			
$Q_r$	reverse charge	$I_F = 3 \text{ A}; V_R = 100 \text{ V}; dI_F/dt = 100 \text{ A/us};$ $T_j = 25 \text{ °C}; Fig. 7$		-	32	-	nC
		$I_F = 3 \text{ A}; V_R = 100 \text{ V}; dI_F/dt = 100 \text{ A/us};$ $T_j = 125 \text{ °C}; Fig. 7$		-	77	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/us};$ $T_j = 25 \text{ °C}; Fig. 7$		-	-	35	ns
		$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{R(meas)} = 0.25 \text{ A};$ $T_j = 25 ^{\circ}\text{C}; \text{ Step Recovery}$		-	-	28	ns
		$I_F = 3 \text{ A}; V_R = 100 \text{ V}; dI_F/dt = 100 \text{ A/us};$ $T_j = 25 \text{ °C}; Fig. 7$		-	27	-	ns
		$I_F = 3 \text{ A}; V_R = 100 \text{ V}; dI_F/dt = 100 \text{ A/us};$ $T_j = 125 \text{ °C}; Fig. 7$		-	41	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 3 \text{ A}; V_R = 100 \text{ V}; dI_F/dt = 100 \text{ A/us};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$		-	2.4	-	Α
		$I_F = 3 \text{ A}; V_R = 100 \text{ V}; dI_F/dt = 100 \text{ A/us};$ $T_j = 125 \text{ °C}; Fig. 7$		-	3.8	-	Α
E <sub>as</sub>	non-repetitive avalanche energy	$I_R = 1.2 \text{ A}; T_{j(init)} = 25 \text{ °C}; L = 15 \text{ mH}$		10.8	-	-	mJ



 $V_o$  = 0.573 V;  $R_s$  = 0.0410 Ω (1)  $T_j$  = 150 °C; typical values (2)  $T_j$  = 150 °C; maximum values (3)  $T_j$  = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage

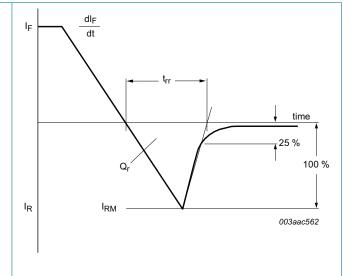


Fig. 7. Reverse recovery definitions; ramp recovery

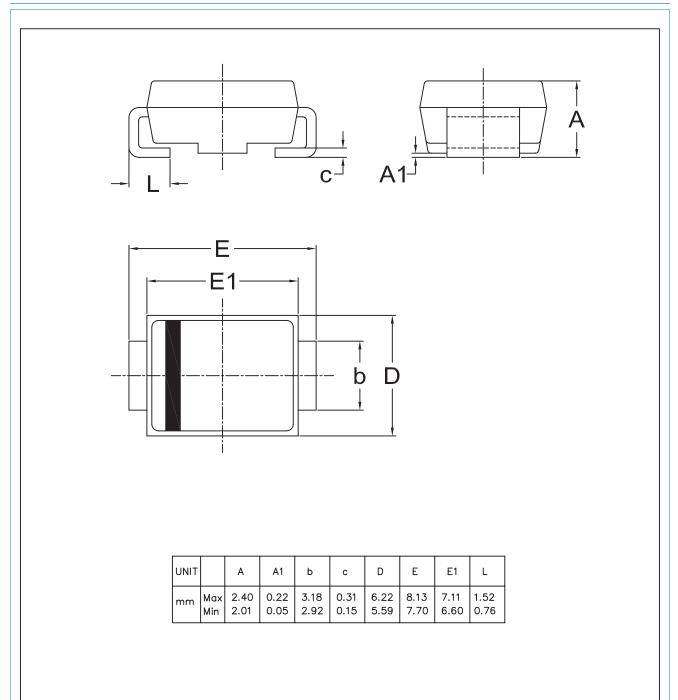
MUR320

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**Ultrafast power diode** 

# 11. Package outline



Remark: Dimensions D and E1 do not include mold flash.

#### Ultrafast power diode

### 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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